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Kind regards,

Team Nexperia



High-voltage switching diodes Rev. 01 — 9 October 2009

Product data sheet

1. **Product profile**

1.1 General description

High-voltage switching diodes, encapsulated in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number	Configuration	Package		Package	
		NXP	JEDEC	configuration	
BAS21W	single	SOT323	SC-70	very small	
BAS21AW	dual common anode				
BAS21SW	dual series				

Very small SMD plastic package

AEC-Q101 qualified

Voltage clamping

Reverse polarity protection

1.2 Features

- High switching speed: $t_{rr} \le 50$ ns Low capacitance: $C_d \le 2 pF$
- Low leakage current
- High reverse voltage: $V_R \le 250 \text{ V}$

1.3 Applications

- High-speed switching
- General-purpose switching

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
l _F	forward current		<u>[1]</u> _	-	225	mA
I _R	reverse current	V _R = 200 V	-	-	100	nA
V _R	reverse voltage		-	-	250	V
t _{rr}	reverse recovery time		[2] _	-	50	ns

[1] Single diode loaded.

[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.



High-voltage switching diodes

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
BAS21W			
1	anode		
2	not connected		3
3	cathode	1 2	1 <u>1</u> 2 006aaa764
BAS21AW			
1	cathode (diode 1)		
2	cathode (diode 2)		3
3	common anode		
BAS21SW			
1	anode (diode 1)		_
2	cathode (diode 2)		3
3	cathode (diode 1), anode (diode 2)		

3. Ordering information

Table 4. Ordering information					
Type number	Package	ackage			
	Name	Description	Version		
BAS21W	SC-70	plastic surface-mounted package; 3 leads	SOT323		
BAS21AW					
BAS21SW					

High-voltage switching diodes

4. Marking

Type number	Marking code ^[1]	
BAS21W	X4*	
BAS21AW	X6*	
BAS21SW	X5*	

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V _R	reverse voltage		-	250	V
I _F	forward current		<u>[1]</u> -	225	mA
			[2] _	125	mA
I _{FRM}	repetitive peak forward current		-	625	mA
I _{FSM} non-rep	non-repetitive peak forward	square wave	[3]		
	current	t _p = 1 μs	-	9	А
		t _p = 100 μs	-	3	А
		t _p = 10 ms	-	1.7	А
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[4] _	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Single diode loaded.

[2] Double diode loaded.

[3] $T_j = 25 \ ^{\circ}C$ prior to surge.

[4] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

High-voltage switching diodes

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	625	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	300	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

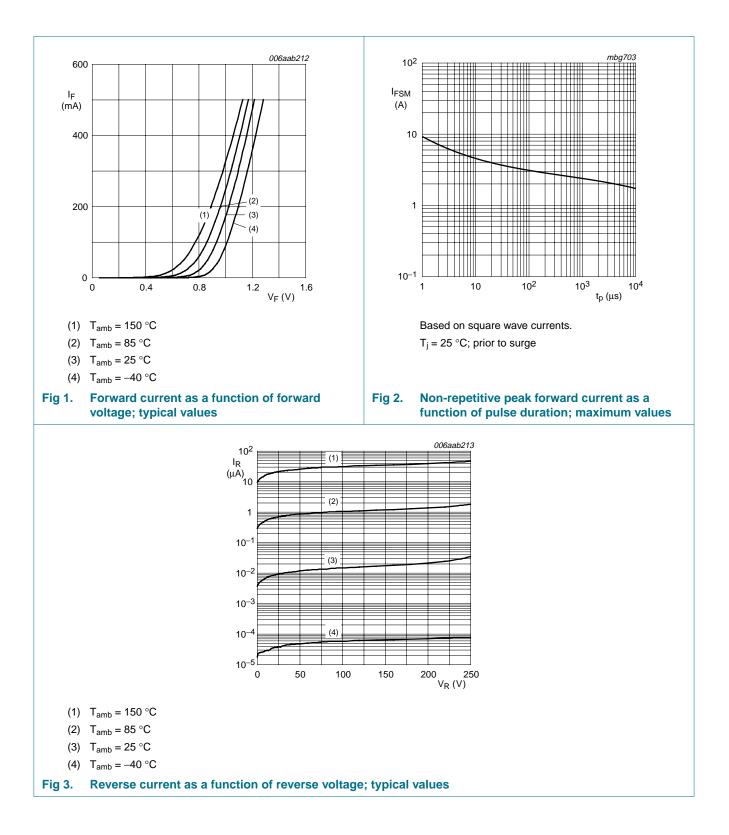
anno —•						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode)					
V _F	forward voltage	I _F = 100 mA	-	-	1.0	V
		I _F = 200 mA	-	-	1.25	V
I _R	reverse current	V _R = 200 V	-	-	100	nA
		$V_R = 200 \text{ V}; \text{ T}_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 0 V	-	-	2	pF
t _{rr}	reverse recovery time		<u>[1]</u> _	-	50	ns

[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

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BAS21W series

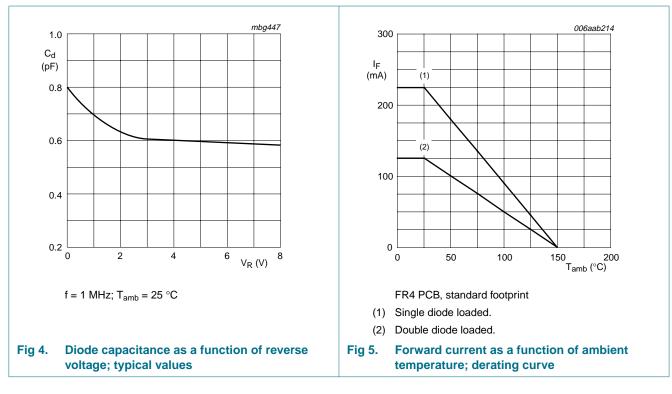
High-voltage switching diodes



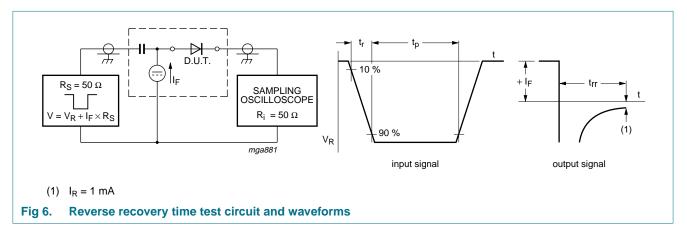
NXP Semiconductors

BAS21W series

High-voltage switching diodes



8. Test information

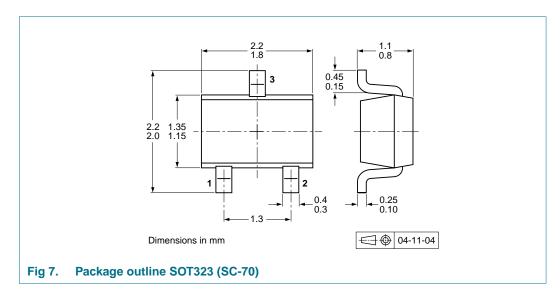


8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

High-voltage switching diodes

9. Package outline



10. Packing information

Table 9.Packing methods

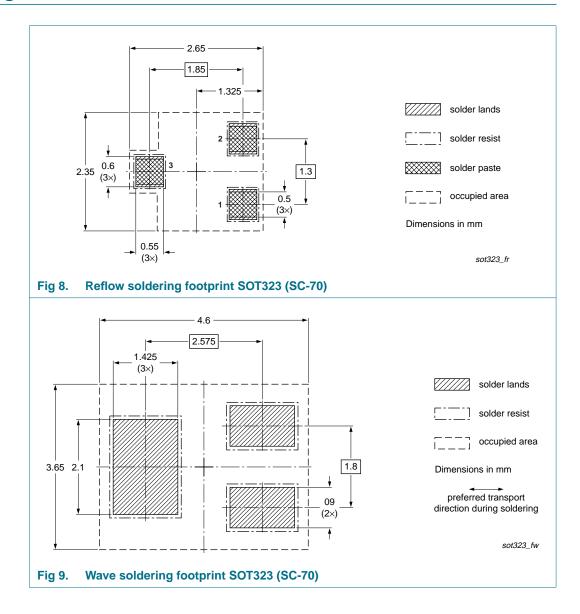
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	je Description		Packing quantity	
			3000	10000	
BAS21W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135	
BAS21AW					
BAS21SW					

[1] For further information and the availability of packing methods, see Section 14.

High-voltage switching diodes

11. Soldering



High-voltage switching diodes

12. Revision history

Table 10. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BAS21W_SER_1	20091009	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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BAS21W_SER_1 Product data sheet

High-voltage switching diodes

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Date of release: 9 October 2009 Document identifier: BAS21W_SER_1

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